



60V NPN ULTRA LOW VCE(sat) TRANSISTOR IN SOT223

Description

A proprietary structure is used in achieving ultra-low $V_{\text{CE(sat)}}$ performance and reduced operating temperature. This has the benefit of reducing thermal management requirements and increasing long-term reliability.

Features

- BVcEo > 60V
- 5.5A Continuous Collector Current
- Low Saturation Voltage V_{CE(sat)} < 45mV @ 1A
- High Current R_{CE(sat)} Typ = 25mΩ
- h_{FE} Characterized Up to 6A
- 2W Power Dissipation
- Fast Switching with Short Storage Time
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: SOT223
- Package Material: Molded Plastic. "Green" Molding Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Solderable per MIL-STD-202, Method 208@3
- Weight: 0.112 grams (Approximate)

Applications

- Medium-power DC-DC converters
- High-side/low-side switches
- Linear voltage regulation

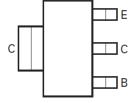
SOT223



Top View



Device Symbol



Top View Pin-Out

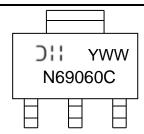
Ordering Information (Note 4)

Orderable Part Number	Pookogo	Marking	Reel Size	Tape Width	Packing	
Orderable Part Number	Package	Warking	(inches)	(mm)	Qty.	Carrier
DXTN69060CE-7	SOT223	N69060C	7	12	1,000	Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



N69060C = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 4 = 2024) WW = Week Code (01 to 53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vcво	80	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	VEBO	7	V
Continuous Collector Current	Ic	5.5	Α
Peak Pulse Current	Ісм	12	Α
Base Current	lв	1	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		2 16		
Power Dissipation Linear Derating Factor	(Note 6)	P _D	1.6 12.8	W mW/°C	
·	(Note 7)		1 8		
	(Note 5)		62.5		
Thermal Resistance, Junction to Ambient	(Note 6)	Reja	78	°C/W	
	(Note 7)		125		
Thermal Resistance, Junction to Lead	(Note 8)	R _{0JL}	21	°C/W	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C		

Notes:

- 5. For a device mounted with the exposed collector pad on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured 5. For a device mounted with the exposed collector pad on 25him x 25him 202 copper that under still air conditions whilst operating in a steady-state.
 6. Same as Note 5, except the device is mounted on 15mm x 15mm 20z copper.
 7. Same as Note 5, except the device is mounted on minimum recommended pad layout.
 8. Thermal resistance from junction to solder-point (at the end of the collector lead).

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	С
Electrostatic Discharge – Charged Device Model	ESD CDM	1,000	V	IV

Note: 9. Refer to JEDEC specification JESD22-A114, JESD22-A115 and JESD22-C101.



Thermal Characteristics and Derating Information

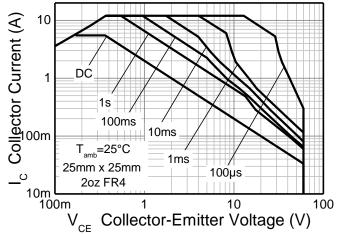


Fig 1. Safe Operating Area

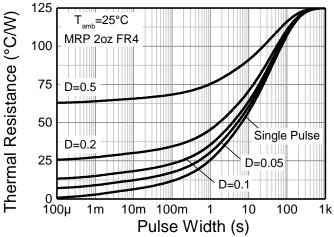


Fig 2. Transient Thermal Impedance

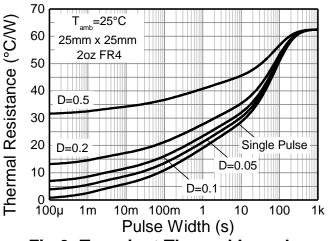


Fig 3. Transient Thermal Impedance

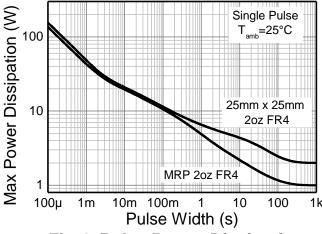


Fig 4. Pulse Power Dissipation

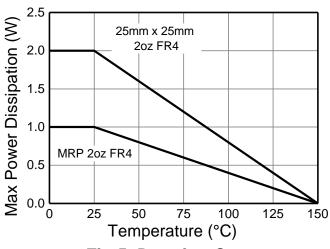


Fig 5. Derating Curve



Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	ВУсво	80	_	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Base Open) (Note 10)	BV _{CEO}	60	_	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	_	_	V	I _E = 100μA
Collector-Base Cutoff Current	Ісво	_	_	100 0.5	nΑ μΑ	V _{CB} = 80V V _{CB} = 80V, T _A = +100°C
Emitter-Base Cutoff Current	I _{EBO}	_	_	100	nA	V _{EB} = 6V
ON CHARACTERISTICS (Note 10)				l.	l.	. ==
Static Forward Current Transfer Ratio	hFE	250 200 80	370 330 170	475 — —	_	I _C = 100mA, V _{CE} = 2V I _C = 2A, V _{CE} = 2V I _C = 6A, V _{CE} = 2V
Collector-Emitter Saturation Voltage	VCE(sat)	1	32 70 80 140 180	45 95 110 180 230	mV	Ic = 1A, IB = 100mA Ic = 1A, IB = 10mA Ic = 2A, IB = 40mA Ic = 5.5A, IB = 550mA Ic = 5.5A, IB = 150mA
Base-Emitter Saturation Voltage	VBE(sat)	_	1,050 890	1,150	mV	$I_C = 5.5A$, $I_B = 550mA$ $I_C = 5.5A$, $I_B = 150mA$
Base-Emitter On Voltage	V _{BE(on)}	_	830	900	mV	Ic =5.5A, VcE = 2V
SWITCHING CHARACTERISTICS						
Transition Frequency	fτ	_	200	_	MHz	$I_C = 100 \text{mA}, V_{CE} = 10 \text{V},$ f = 100 MHz
Input Capacitance	Cibo	_	380	_	pF	$V_{EB} = 0.5V, f = 1MHz$
Output Capacitance	C _{obo}	_	23	_	pF	$V_{CB} = 10V, f = 1MHz$
Delay Time	td	_	81	_	ns	V 04V I 750A
Rise Time	tr	_	64	_	ns	$V_{CC} = 24V$, $I_{C} = 750$ mA, $I_{B1} = -I_{B2} = 15$ mA.
Storage Time	ts	_	640	_	ns	☐ IB1 = -IB2 = 15mA. - See Fig 6.
Fall Time	t _f	_	78	_	ns	000 1 ig 0.
Delay Time	t _d	_	87	_	ns	10)/ 1 750 1
Rise Time	tr	_	117		ns	Vcc = 48V, Ic = 750mA,
Storage Time	ts	_	510	_	ns	$I_{B1} = -I_{B2} = 15\text{mA}$ - See Fig 6.
Fall Time	t _f	_	101	_	ns	000 Tig 0.

Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%

Timing Waveform

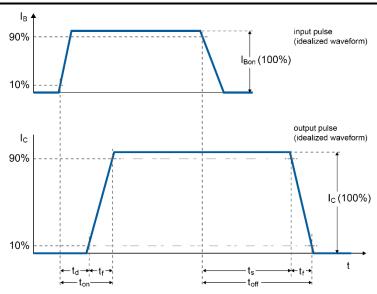


Fig 6. Timing Waveform



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

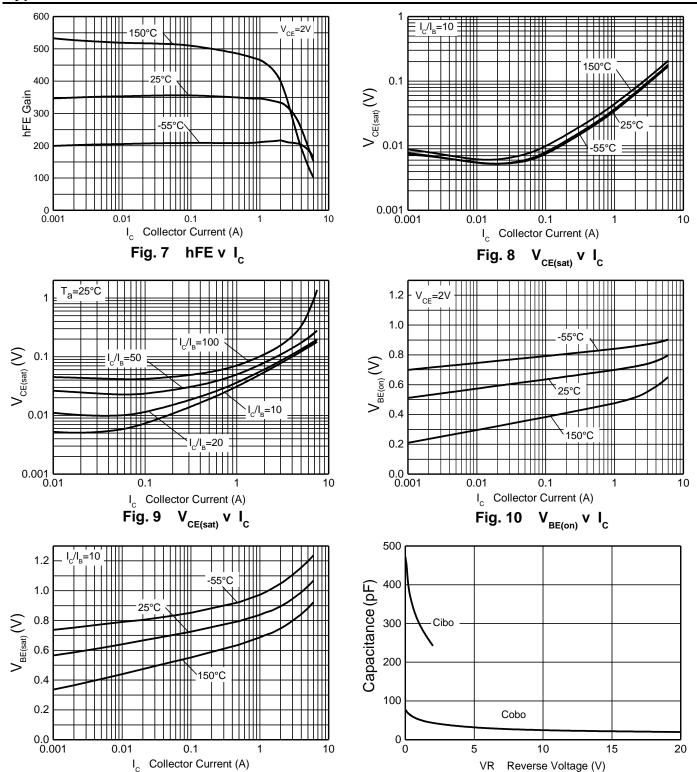


Fig. 11 V_{BE(sat)} v I_C



Application Notes

Figure 13 shows the DXTN69060CE as a low-side switch. When driving high-current inductive loads, it is recommended to apply appropriate protective measures to manage the kick-back voltage that builds up due to the collapse of the inductor's magnetic field after a switch-off event. The voltage spikes that originate this way can potentially overstress the device above its Maximum Ratings. During evaluation, ensure that the Collector-Emitter Voltage stays below V_{CEO} rating of 60V. An easy way to suppress induced voltage spikes is to place an additional free-wheeling diode in parallel with the load as shown in Figure 14.

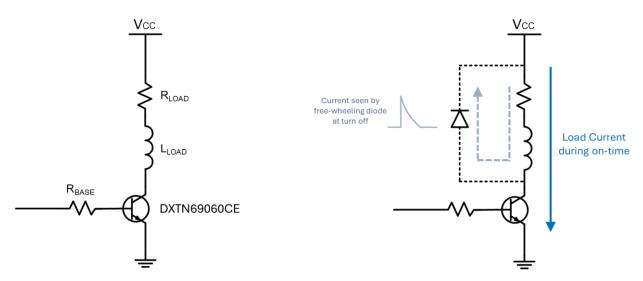


Fig. 13 DXTN69060CE in a low-side switch configuration

Fig. 14 Additional free-wheeling diode across inductive load for voltage spikes suppression

The appropriate free-wheeling diode should have:

- An Average Rectified Output Current (Io) rating of at least twice the full Load Current
- A Working Peak Reverse Voltage (V_{RWM}) equal to the voltage applied to the load (minimum) or twice its value (recommended)

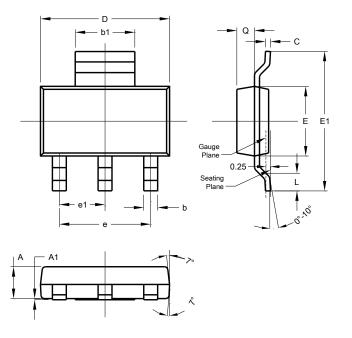
For example, in the figures above, $V_{CC} = 24V$ and $I_{LOAD} = 3A$. The PDS760 Schottky Barrier Rectifier with I_0 =7A and V_{RWM} =60V will protect the transistor from turn-off inductive voltage spikes and ensure a safe system operation.



Package Outline Dimensions

Please see https://www.diodes.com/package-outlines.html for the latest version.

SOT223

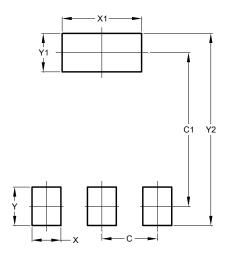


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A 1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see https://www.diodes.com/package-outlines.html for the latest version.

SOT223



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
٧a	0.00



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